

# Cold excitons

## Introduction

- **Excitons and electron-hole plasma in semiconductors**
- **Exciton condensation**
- **Experimental systems**
- **Indirect excitons in coupled quantum wells**

## Phenomena in cold exciton gases

- **Stimulated scattering**
- **Pattern formation and transport**
- **Coherence and condensation**

## Control of excitons, excitons in potential landscapes

- **Optical traps**
- **Excitonic circuits**
- **Excitons in traps**
- **Excitons in lattices**

## Spin transport of excitons

## Most recent studies

- **Topological defects in interference pattern**
- **Spin pattern formation**

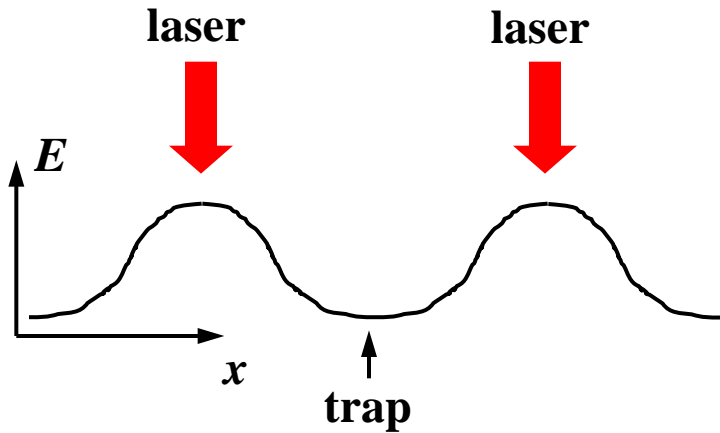
## optical traps



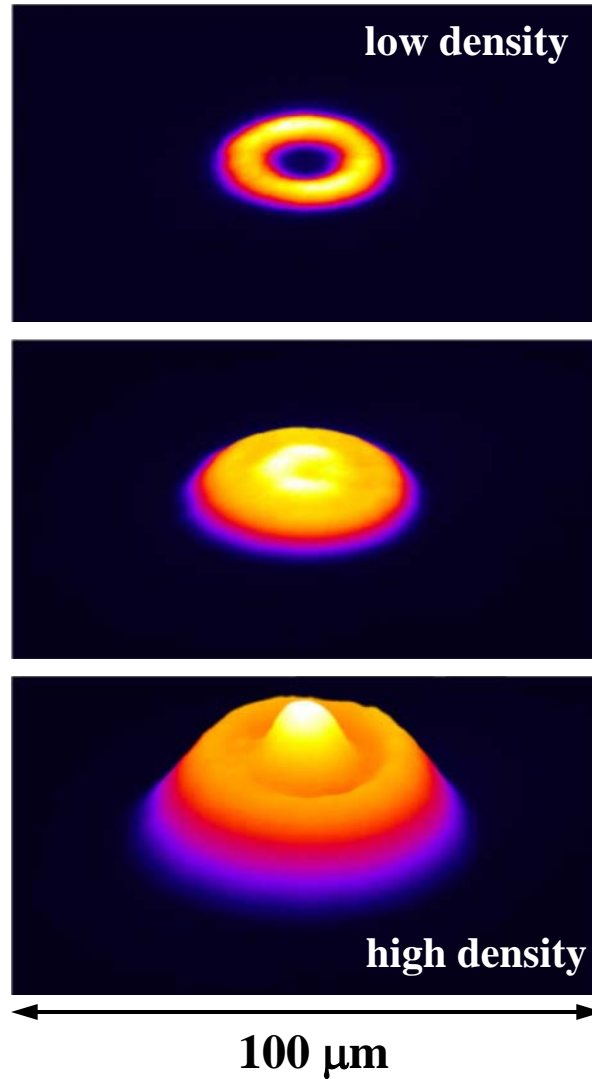
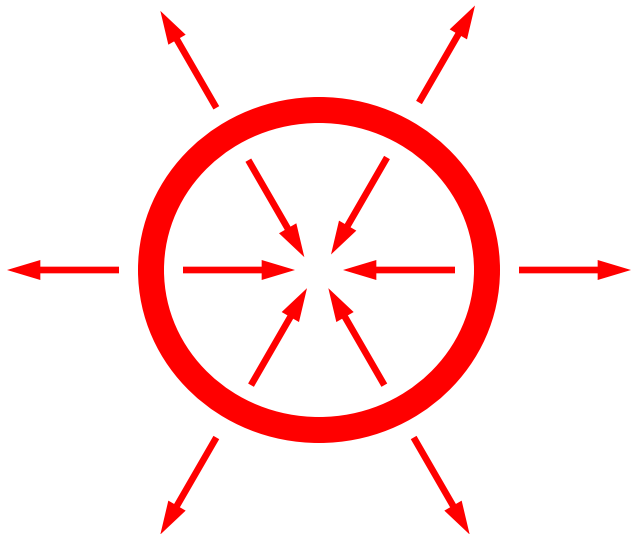
**in biology:**  
manipulation of DNA, viruses  
& cells by optical tweezers

**in atomic physics:**  
**development of methods to cool  
and trap atoms with laser light**  
→ atom BEC in optical traps

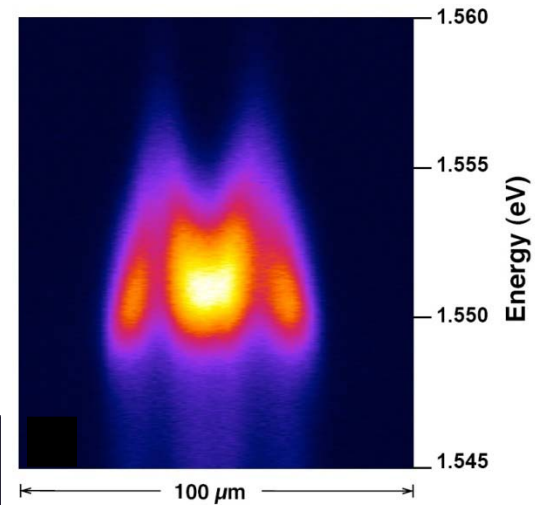
# Trapping of cold excitons with laser light



- can be switched on and off
- no heating in the trap center  
→ excitons are cold in the trap
- ability to form various potential patterns



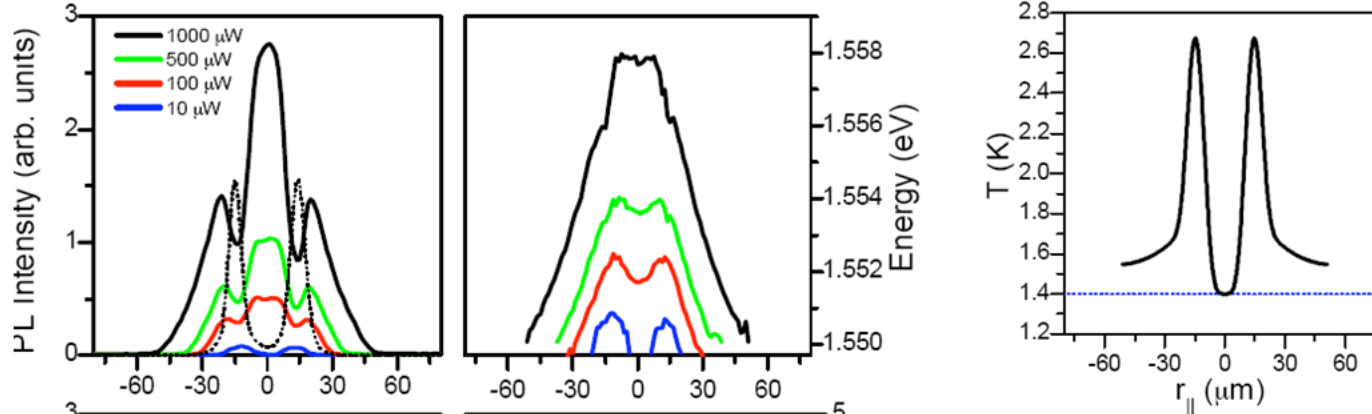
experimental implementation



A. Hammack, M. Griswold, L.V. Butov, A.L. Ivanov, L. Smallwood, A.C. Gossard, PRL 96, 227402 (2006)

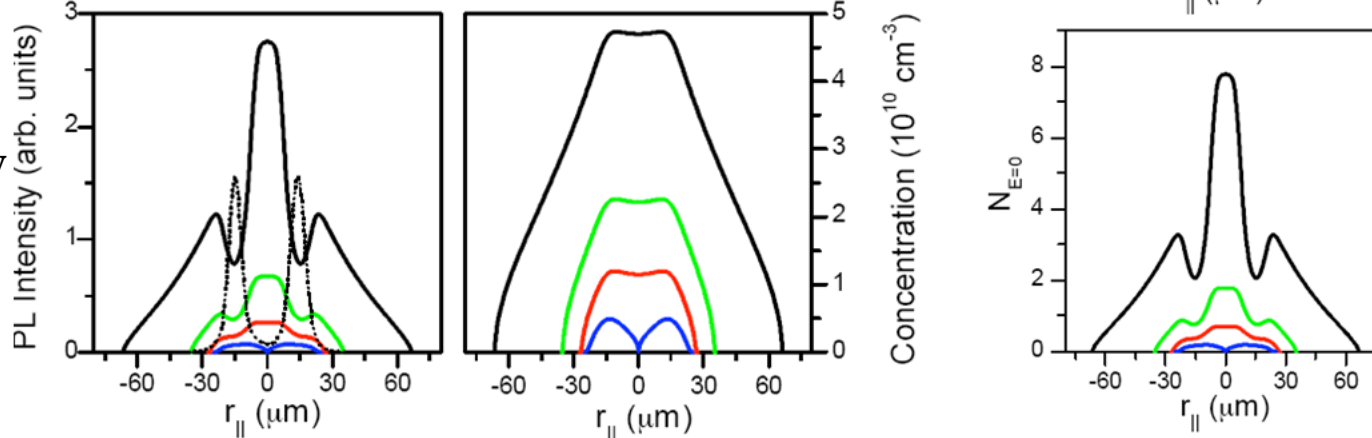
# Experimental data for exciton PL, density, and energy distribution in laser-induced traps vs theory

exp



excitons are cold in the trap center with  $T_X = T_{lattice}$

theory



the trapping of a highly degenerate Bose gas of excitons in laser induced traps

$$U_{trap}(x, y) = \delta E(x, y) = \frac{4\pi e^2 d}{\epsilon} n(x, y)$$

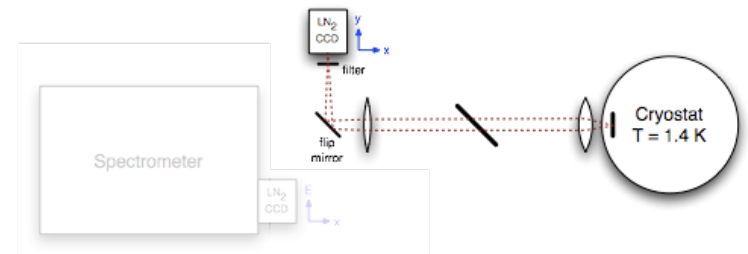
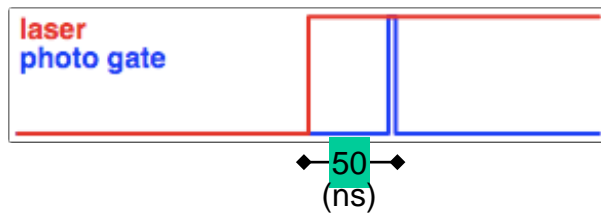
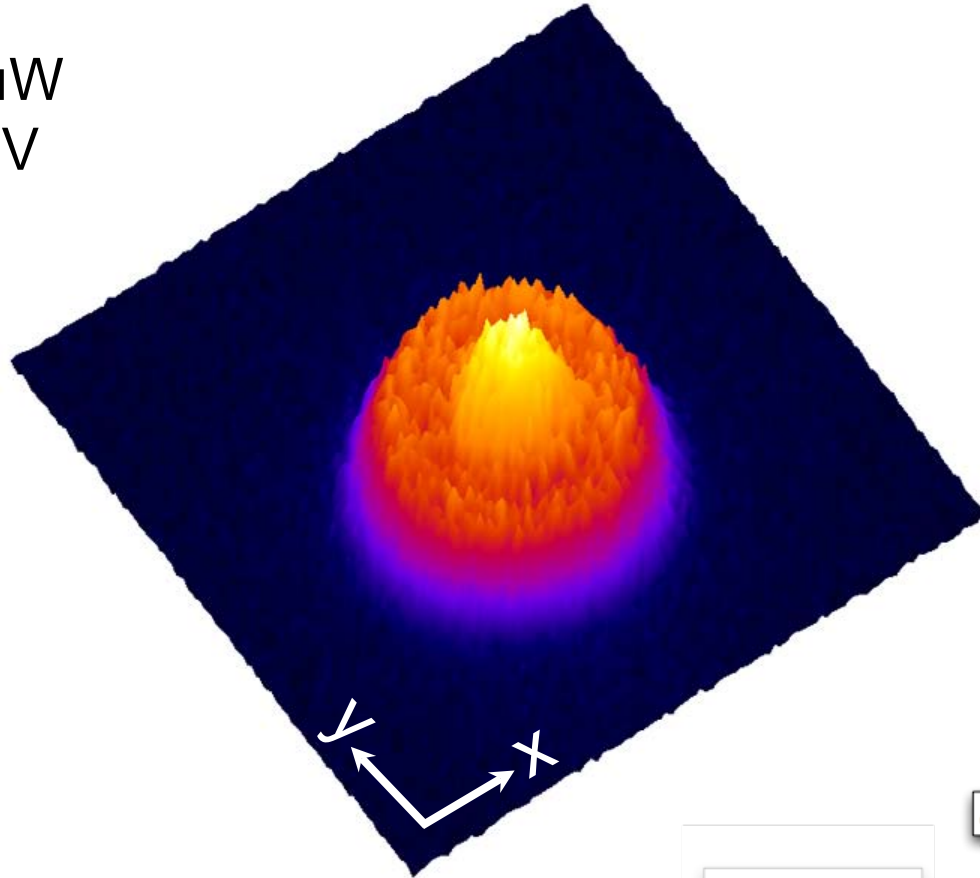
$$\left. \begin{array}{l} \delta E \approx 8 \text{ meV} \Rightarrow n \approx 5 \times 10^{10} \text{ cm}^{-2} \\ T \approx T_{bath} = 1.4 \text{ K} \end{array} \right\} \rightarrow N_{E=0} = e^{T_{dB}/T_X} - 1 \approx 8$$

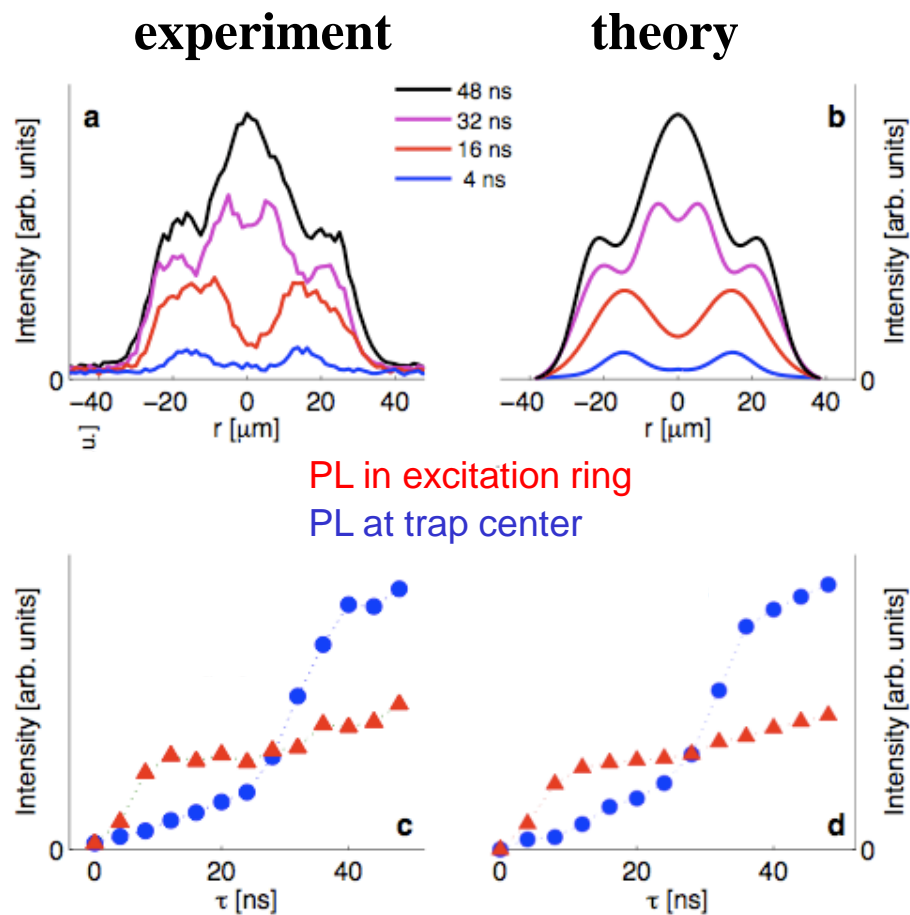
# Exciton collection to laser-induced trap

$$P_{\text{ex}} = 75 \mu\text{W}$$

$$V_g = -1.2 \text{ V}$$

$$\delta = 4 \text{ ns}$$





**observed hierarchy of times**

***(exciton cooling time) < (trap loading time) < (exciton lifetime in the trap)***

$$T_{\text{cooling to } 1.5 \text{ K}} < 4 \text{ ns}$$

$$\tau_{\text{loading}} \sim 40 \text{ ns}$$

$$\tau_{\text{lifetime}} \sim 50 \text{ ns} - 10 \mu\text{s}$$

**is favorable for creating a dense and cold exciton gas in the traps  
and its control *in situ***

# Excitonic circuits

# Excitonic circuits

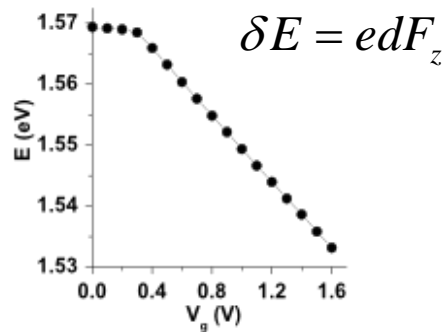
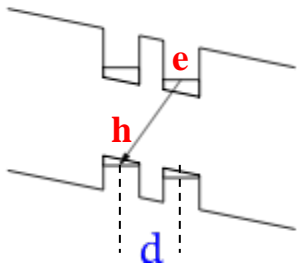
the ability to control electron fluxes by an applied gate voltage

electronic circuit devices

mesoscopics

the field which concerns electron transport in a potential landscapes

potential energy of indirect excitons can be controlled by voltage



in-plane potential landscapes  
can be created for excitons by voltage pattern  
e.g. circuit devices, traps, lattices

the ability to control exciton fluxes by an applied gate voltage

excitonic circuit devices

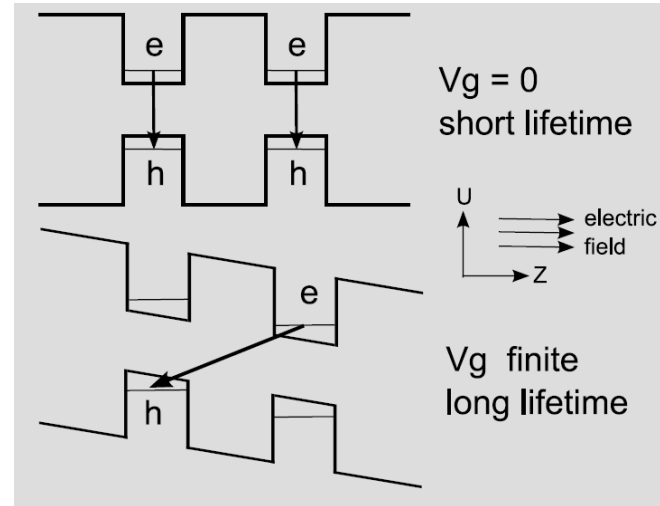
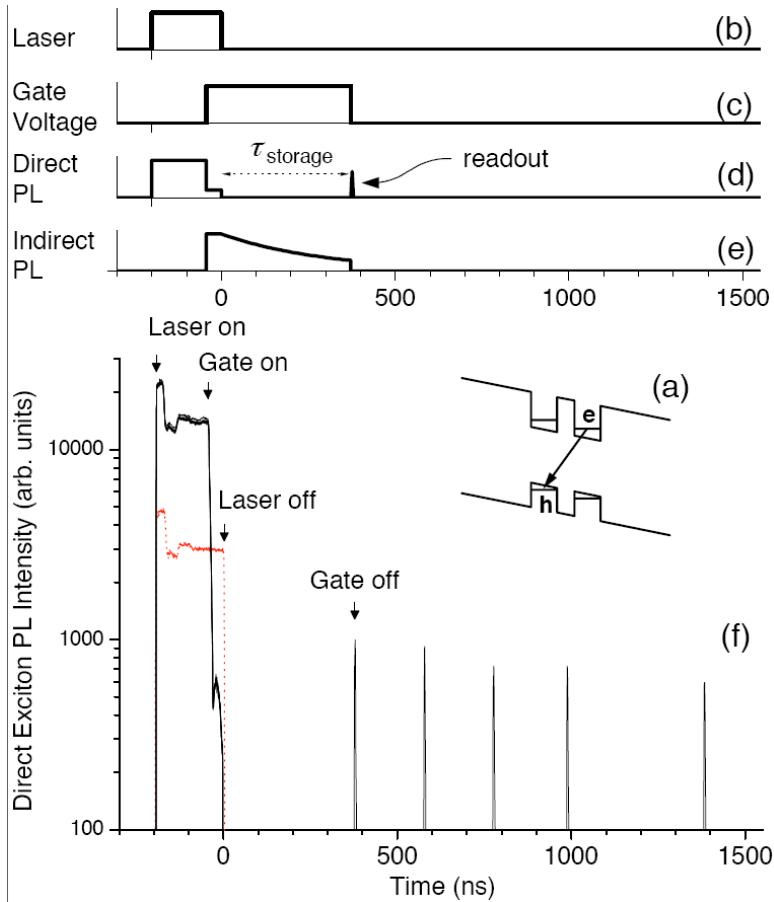
mesoscopics of bosons

in semiconductors

delay between signal processing and optical communication is effectively eliminated in excitonic devices → advantage in applications where interconnection speed is important

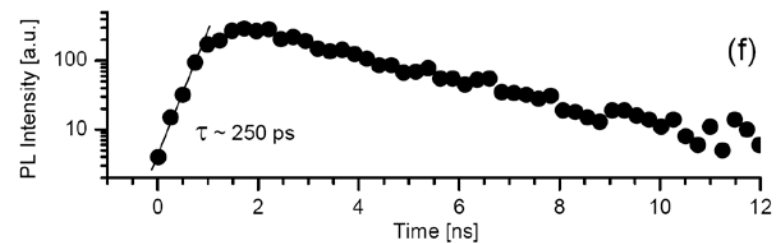


# Storage



**store photons in the form of indirect excitons**

**storage and release of photons is controlled by gate voltage pulses**



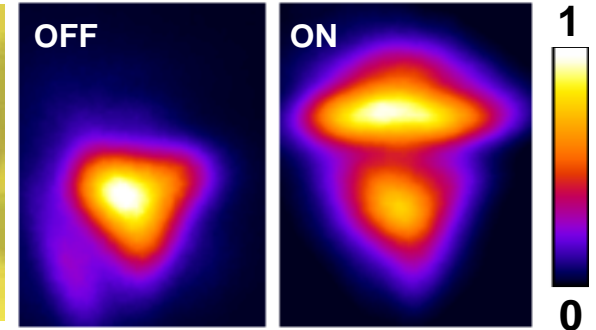
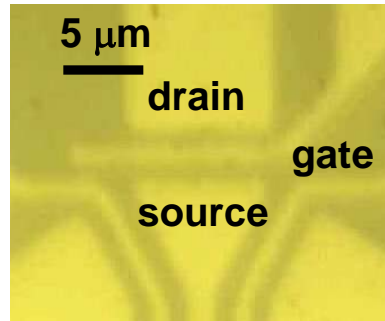
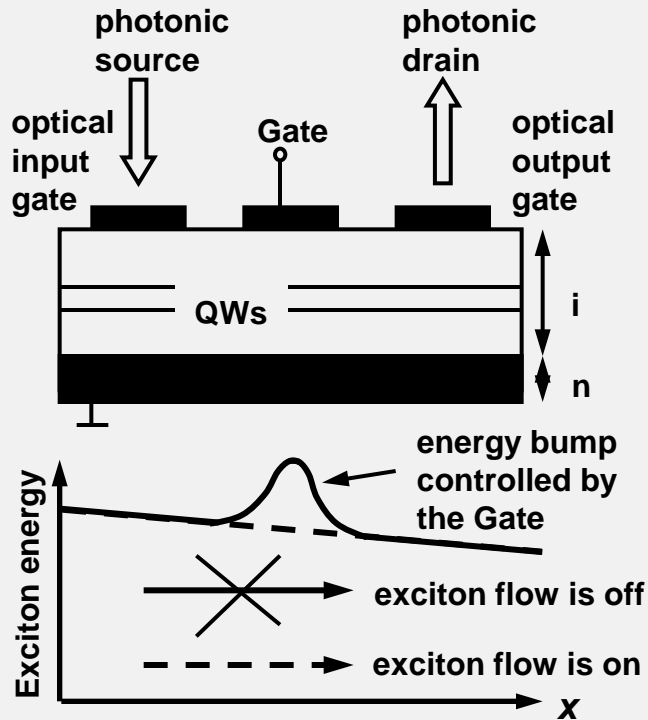
**prototype of storage device reaches sub-ns switching time and several  $\mu\text{s}$  storage time**

A.G. Winbow, A.T. Hammack, L.V. Butov, A.C. Gossard, Nano Lett. 7, 1349 (2007)

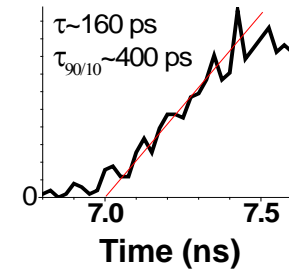
A.G. Winbow, L.V. Butov, A.C. Gossard, JAP 104, 063515 (2008)

# Excitonic Transistor

operation principle of excitonic transistor  
similar to electronic FET  
with excitons in place of electrons



switching  
from  
OFF to ON



- *Fast*: switching time combined with the interconnection time for the first proof-of-principle excitonic transistor was  $\sim 0.2$  ns
- *Compact*: In the first proof-of-principle excitonic transistor the distance between the source and drain was  $3 \mu\text{m}$
- *Scalable*: have architecture and operation principle similar to electronic FET

*Major challenges*: Finite exciton lifetime  
Finite exciton binding energy

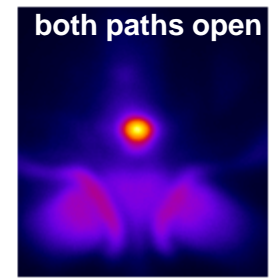
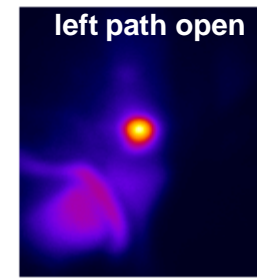
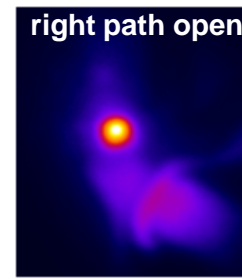
A.A. High, A.T. Hammack, L.V. Butov, M. Hanson, A.C. Gossard, Opt. Lett. 32, 2466 (2007)

A.A. High, E.E. Novitskaya, L.V. Butov, M. Hanson, A.C. Gossard, Science 321, 229 (2008)

# Excitonic IC (EXIC) with 3 Excitonic Transistors

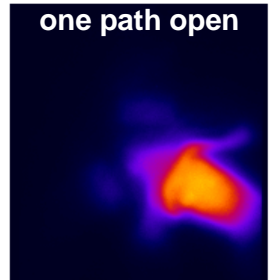
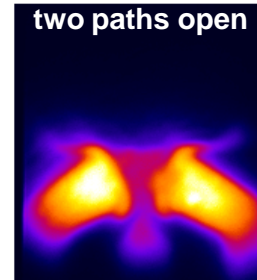
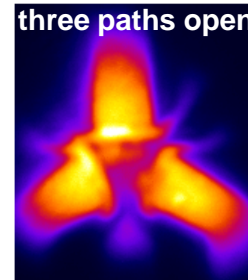
## Prototype EXIC performs directional switching

Flux of excitons photoexcited at ● is directed by gate control



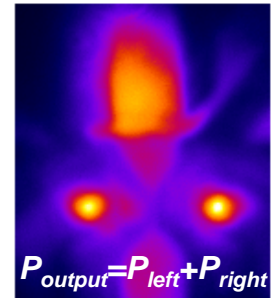
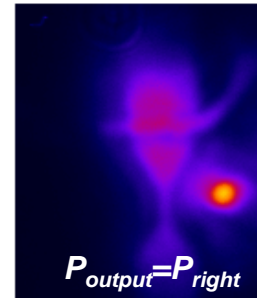
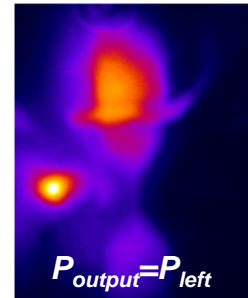
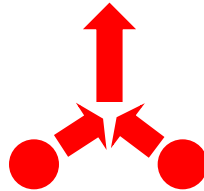
## Prototype EXIC performs directional switching

Flux of excitons photoexcited at ● is directed by gate control

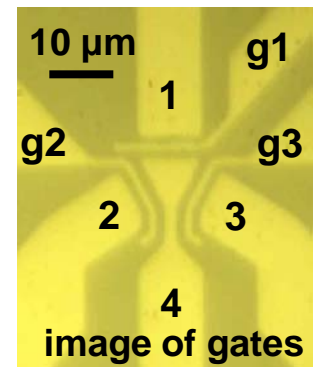


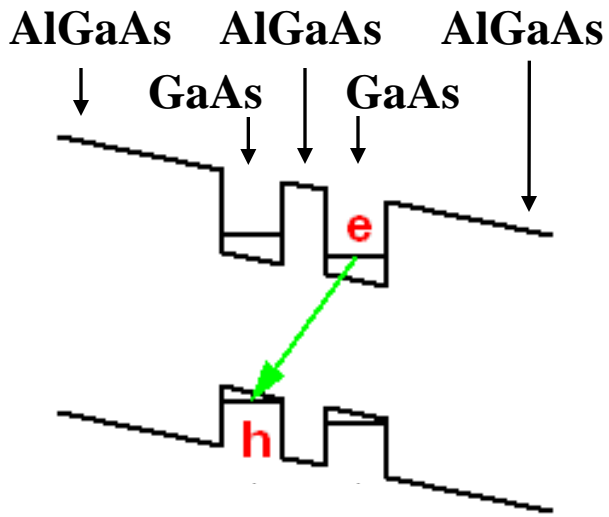
## Prototype EXIC performs flux merging

Two fluxes of excitons photoexcited at ● are combined by gate control. The device can implement sum operation and logic gates.



A.A. High, E.E. Novitskaya, L.V. Butov, M. Hanson, A.C. Gossard, Science 321, 229 (2008)





### GaAs/AlGaAs CQW

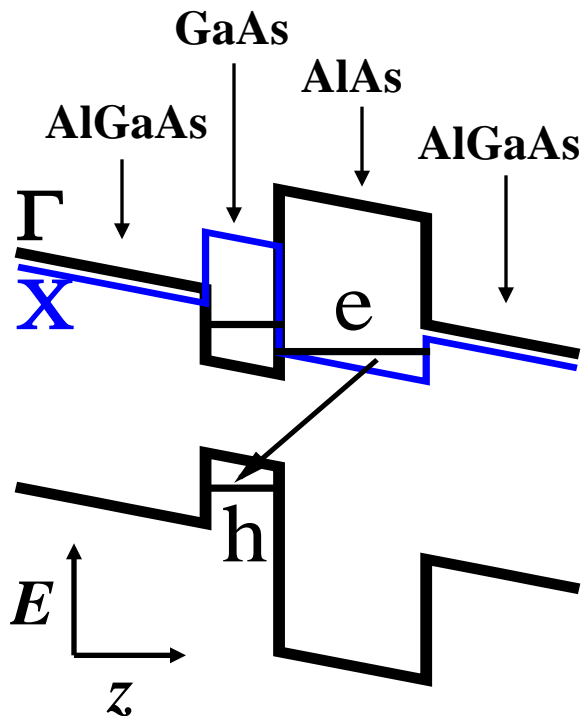
$d \approx 12 \text{ nm}$

$E_{ex}/k_B \sim 40\text{K}$

#### operation at $T = 1.5 \text{ K}$ :

A.A. High, A.T. Hammack, L.V. Butov, M. Hanson, A.C. Gossard, Opt. Lett. 32, 2466 (2007)

A.A. High, E.E. Novitskaya, L.V. Butov, M. Hanson, A.C. Gossard, Science 321, 229 (2008)



### AlAs/GaAs CQW

$d \approx 3\text{nm}$

$E_{ex}/k_B \sim 100\text{K}$

makes possible the operation of excitonic devices above the temperature of liquid Nitrogen

#### operation up to $\sim 100 \text{ K}$ :

G. Grosso, J. Graves, A.T. Hammack, A.A. High, L.V. Butov, M. Hanson, A.C. Gossard, Nature Photonics 3, 577 (2009)

# Excitons in traps

## Early works on electrostatic trapping of indirect excitons

S. Zimmermann, A. Govorov, W. Hansen, J. Kotthaus, M. Bichler, W. Wegscheider, PRB 56, 13414 (1997)

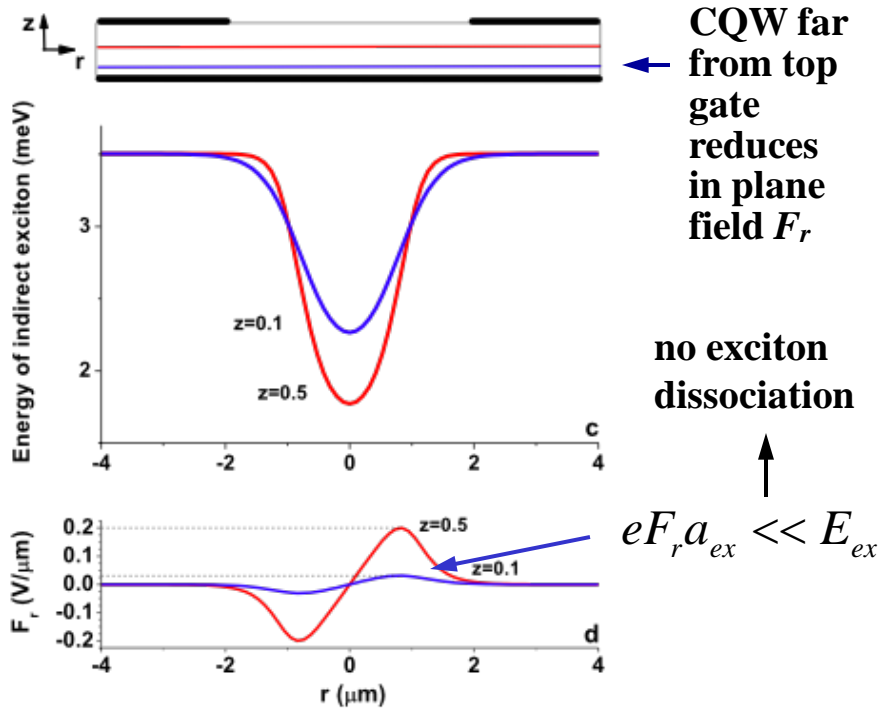
T. Huber, A. Zrenner, W. Wegscheider, M Bichler. Phys. Stat. Sol. (a) 166, R5 (1998)

## Obstacle in early works → in-plane electric field dissociated excitons

## Solution: to position CQW layers closer to the homogeneous bottom electrode

1999 – calculations, 2005 – experiment

A.T. Hammack, N.A. Gippius, Sen Yang, G.O. Andreev, L.V. Butov, M. Hanson, A.C. Gossard, cond-mat/0504045; JAP 99, 066104 (2006)



dissociation rate vs  $F_r$

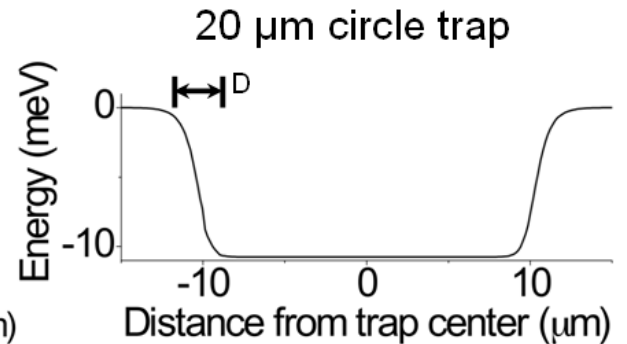
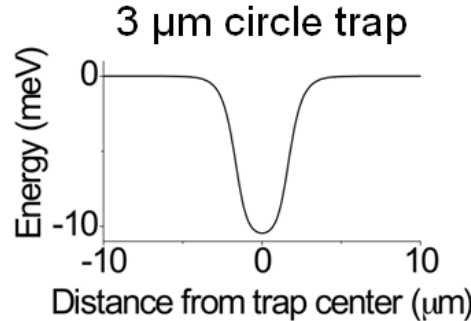
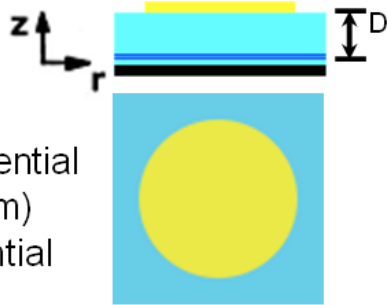
$$\frac{\Gamma_{2D}}{R_y} = \frac{64}{\sqrt{\pi}} \left[ \frac{R_y}{eF_{\parallel} a_0} \right]^{1/2} \exp \left[ -\frac{32R_y}{3eF_{\parallel} a_0} \right]$$

D.A.B. Miller, D.S. Chemla,  
 T.C. Damen, A.C. Gossard,  
 W. Wiegmann, T.H. Wood,  
 C.A. Burrus, PRB 32, 1043 (1985)

# Diamond-shaped traps

## Circle Trap

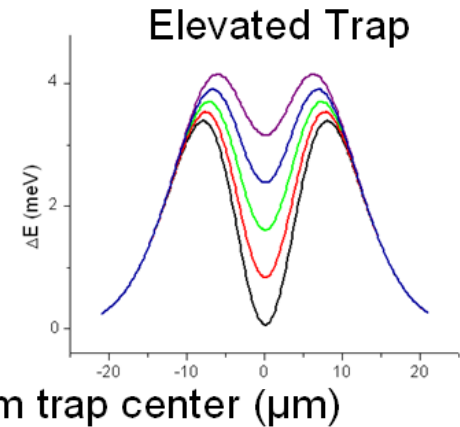
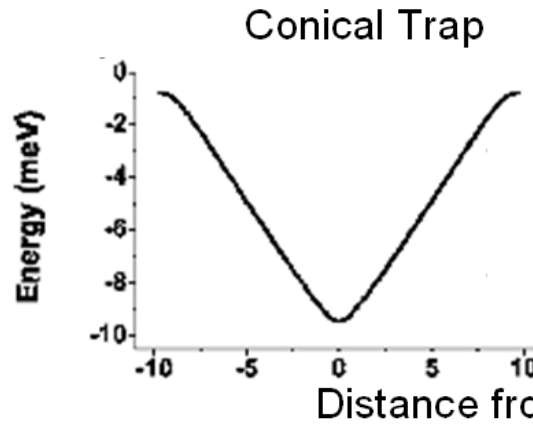
- single electrode
- parabolic-like potential for small radii ( $<3\mu\text{m}$ )
- box-shaped potential for large radii



## Concentric Rings Trap

- multiple electrodes
- versatile potential profiles

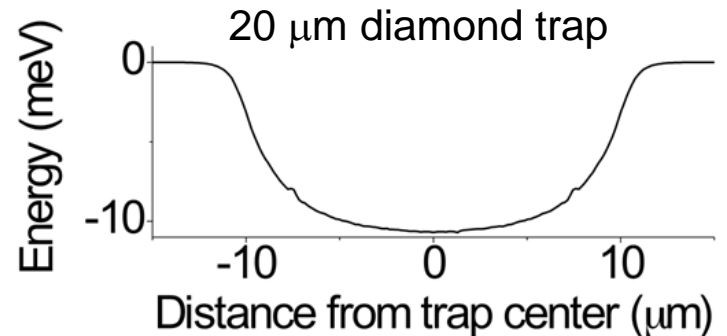
A.T. Hammack, N.A. Gippius,  
Sen Yang, G.O. Andreev,  
L.V. Butov, M. Hanson,  
A.C. Gossard,  
JAP 99, 066104 (2006)



## Diamond Trap

- single electrode
- parabolic-like trap even for large lengths

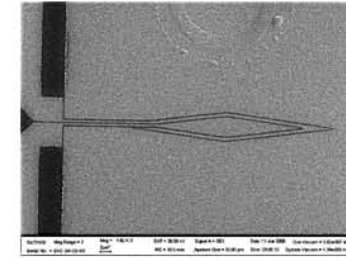
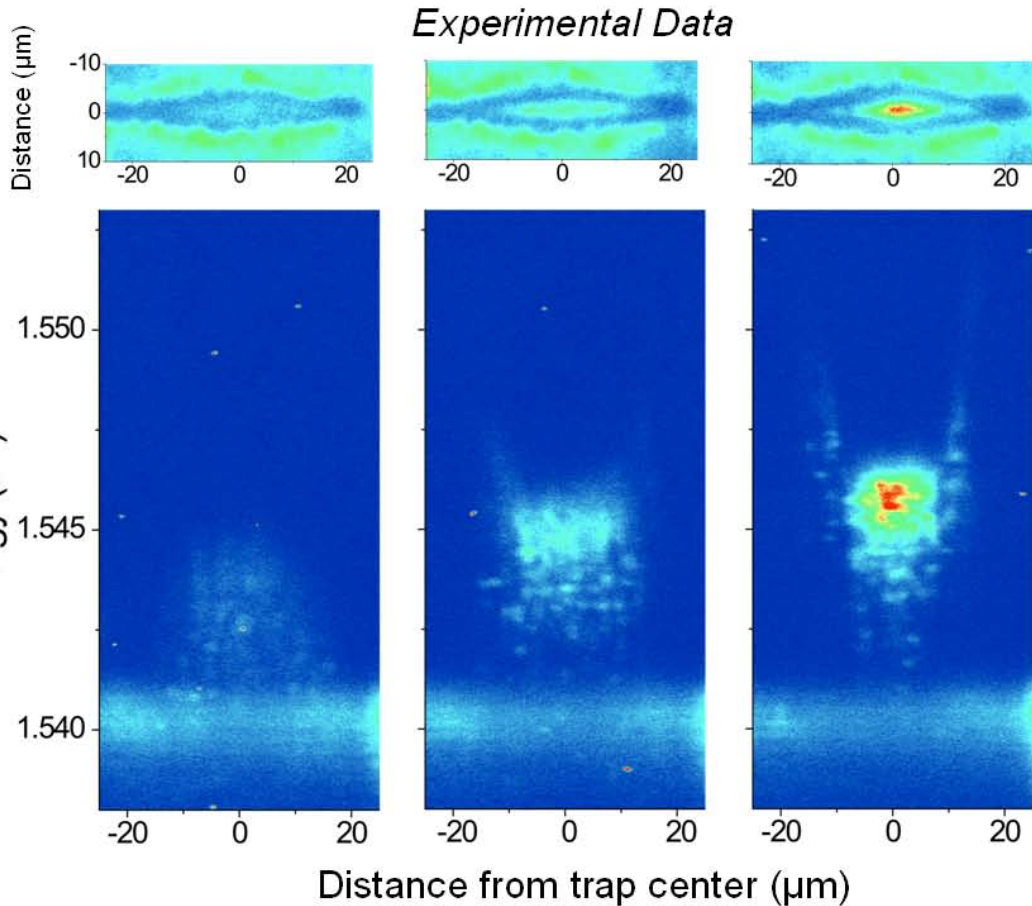
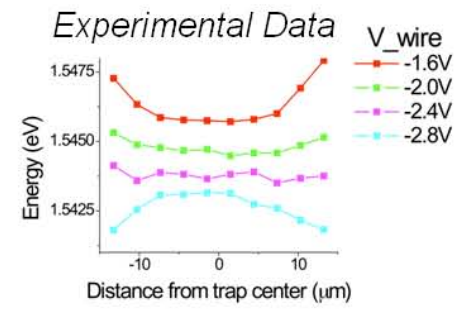
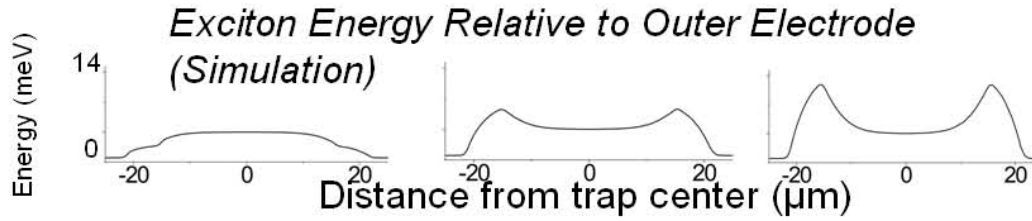
↓  
collect many excitons  
to the trap center



A.A. High, A.K. Thomas, G. Grosso, M. Remeika, A.T. Hammack, A.D. Meyertholen, M.M. Fogler, L.V. Butov,  
M. Hanson, A.C. Gossard, PRL 103, 087403 (2009)



# Excitons in Elevated Diamond Trap



higher energy excitons escape the elevated trap at a higher rate



the excitons in the elevated trap undergo evaporative cooling

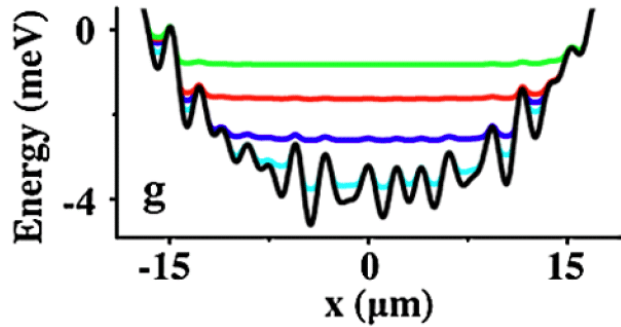
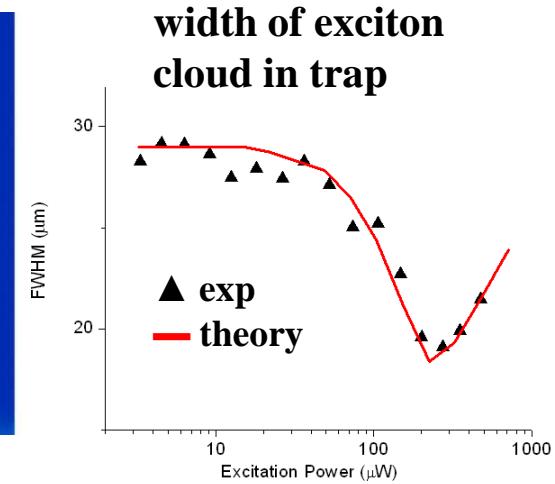
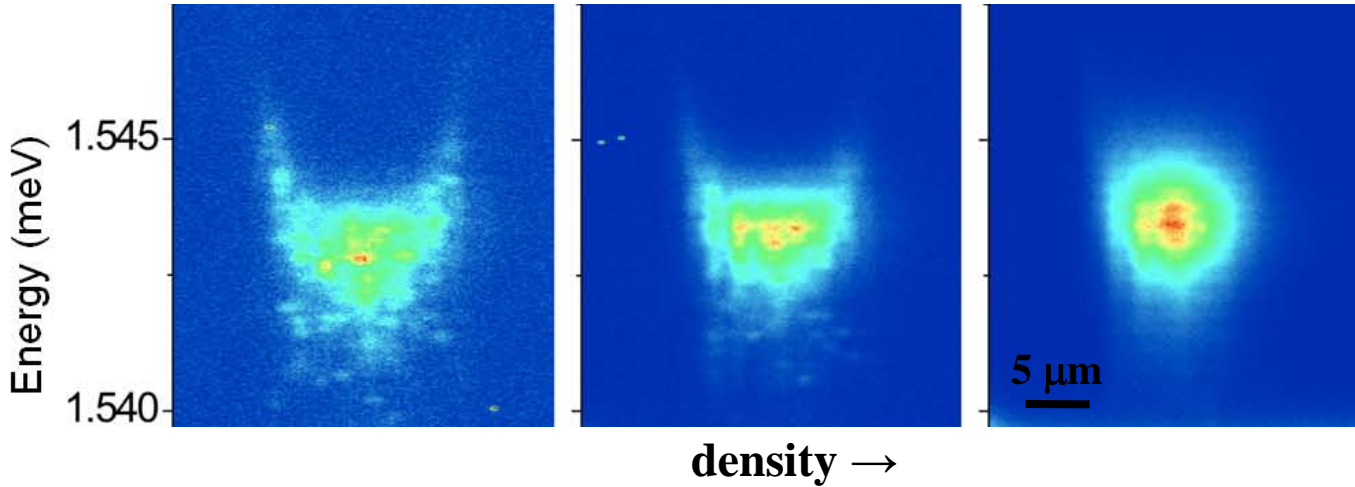
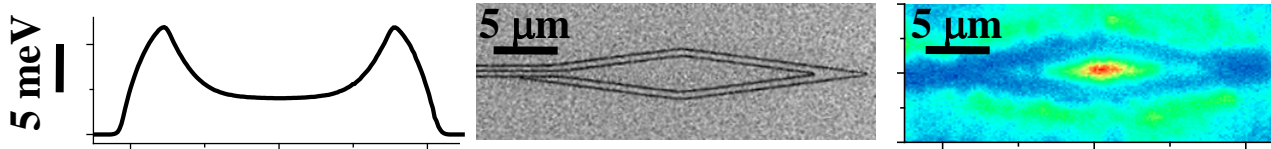


A.A. High, A.T. Hammack, L.V. Butov, L. Mouchliadis, A.L. Ivanov, M. Hanson, A.C. Gossard, Nano Lett. 9, 2094 (2009)

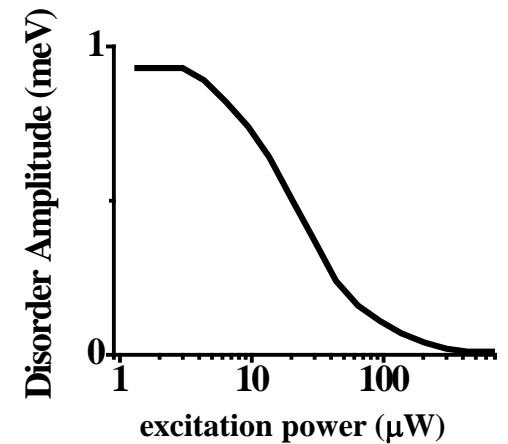
A.A. High, A.K. Thomas, G. Grosso, M. Remeika, A.T. Hammack, A.D. Meyertholen, M.M. Fogler, L.V. Butov, M. Hanson, A.C. Gossard, PRL 103, 087403 (2009)



# Collection of exciton cloud to trap center with increasing density



repulsive interaction  
 ↓  
 screening of disorder  
 ↓  
 collection to trap bottom  
 ↓  
 cold exciton gas in trap



can be controlled in situ like traps for cold atoms

# Excitons in lattices

# Atoms in lattices

M. Greiner, O. Mandel, T. Esslinger, T.W. Hansch, I. Bloch, Nature 415, 39, (2002)

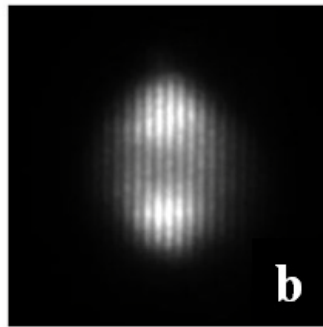
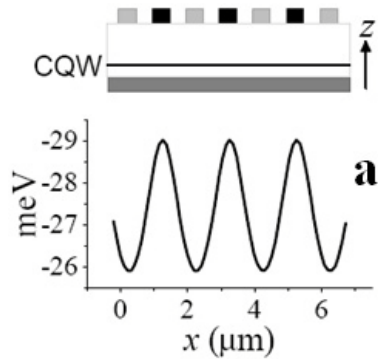
J.K. Chin, D.E. Miller, Y. Liu, C. Stan, W. Setiawan, C. Sanner, K. Xu, W. Ketterle, Nature 443, 961 (2006)

**atoms in lattices – system with controllable parameters**



**use atoms in lattices to emulate solid state materials**

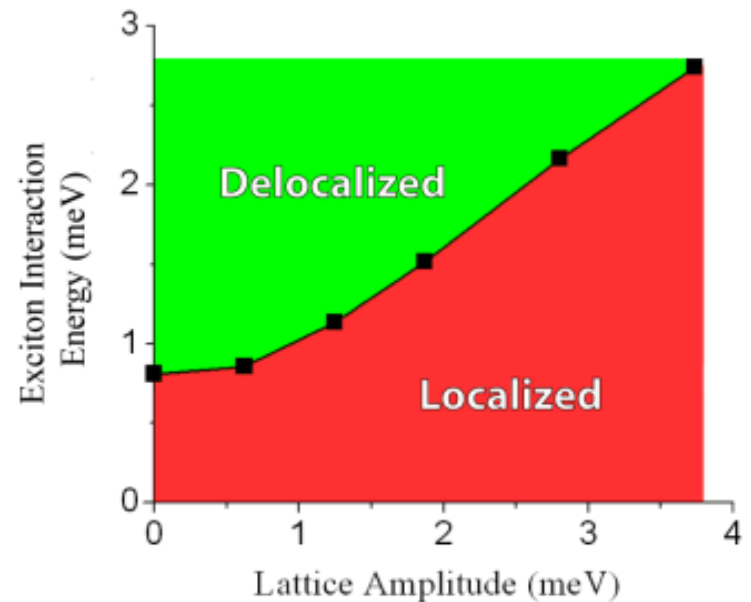
# Excitons in lattices



**controllable: exciton density, interaction, mass  
lattice amplitude, structure, constant**



**a tool with a number of control knobs  
for studying the physics of excitons**



M. Remeika, J. Graves, A.T. Hammack, A.D. Meyertholen, M.M. Fogler, L.V. Butov, M. Hanson, A.C. Gossard, PRL 102, 186803 (2009)

# Transport of electrons, holes, excitons, and polaritons via SAW

C. Rocke, S. Zimmermann, A. Wixforth, J.P. Kotthaus, G. Böhm, G. Weimann, PRL 78, 4099 (1997)

P.V. Santos, M. Ramsteiner, R. Hey, PSS B 215, 253 (1999)

J. Rudolph, R. Hey, P.V. Santos, PRL 99, 047602 (2007)

## Electrostatic conveyers for excitons

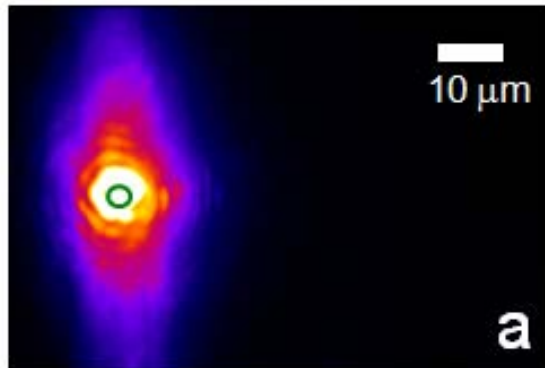
conveyers are created by applying AC voltages to lattice electrodes → traveling lattice

wavelength ← electrodes

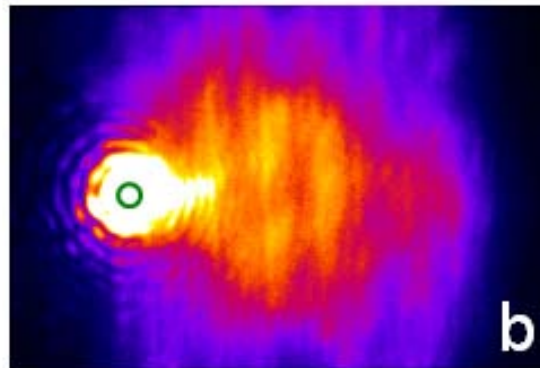
amplitude ← voltage

speed ← frequency

conveyer off



conveyer on



study dynamic LDT  
with varying  
conveyer amplitude  
conveyer speed  
exciton density

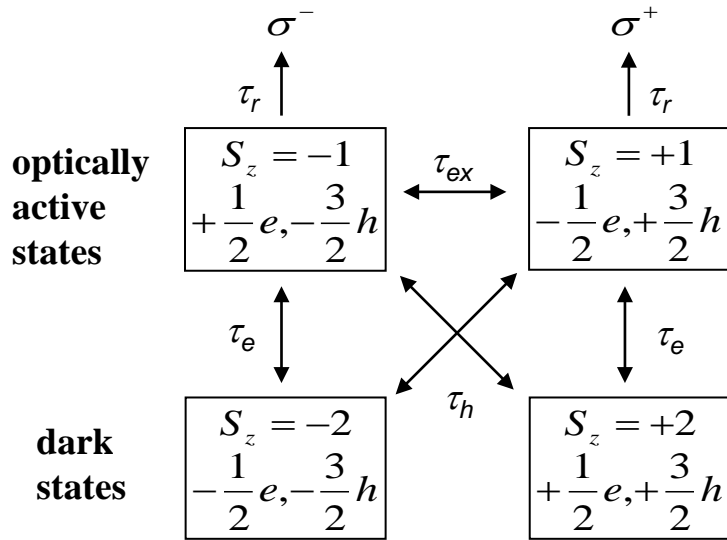
A.G. Winbow, J.R. Leonard, Y.Y. Kuznetsova, M. Remeika, A.A. High, E. Green, A.T. Hammack, L.V. Butov, J. Wilkes, A.L. Ivanov, M. Hanson, A.C. Gossard, unpublished

# **Spin transport of excitons**

**exciton spin transport over substantial distances requires**

- **exciton transport over substantial distances**
- **long spin relaxation time**

# Spin-Flip Pathways



M.Z. Maialle, E.A. de Andrada e Silva,  
L.J. Sham, PRB 47, 15776 (1993)

## polarization relaxation time

$$\tau_P^{-1} = 2(\tau_e + \tau_h)^{-1} + \tau_{ex}^{-1}$$

$$P = \frac{I_+ - I_-}{I_+ + I_-}$$

$\tau_{ex}$  is determined by exchange  
interaction between  $e$  and  $h$

$$\tau_{ex} \propto \tau_r^2$$

control  $\tau_p$  by changing  $e$ - $h$  overlap

**GaAs SQW**  
**direct exciton**

$$\tau_P \sim \tau_{ex}$$

**fast depolarization**  
**within tens of ps**

**GaAs CQW**  
**indirect exciton**  
with small  $e$ - $h$  overlap

$$\tau_P \sim \tau_e / 2$$

**orders of magnitude**  
**enhancement of exciton**  
**spin relaxation time**

**makes possible**  
**exciton spin transport**  
**over substantial distances**

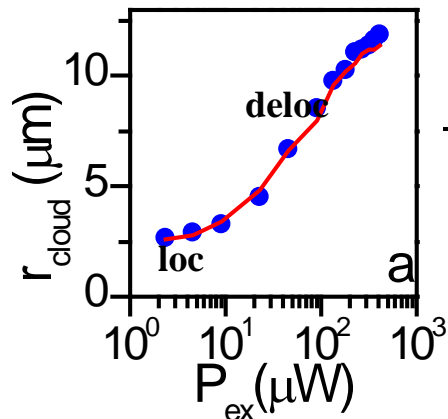
$$\Delta_{\text{bright-dark}} \propto \tau_r^{-1}$$

**GaAs SQW**  
**direct exciton**  
 $\sim 0.1 \text{ meV}$

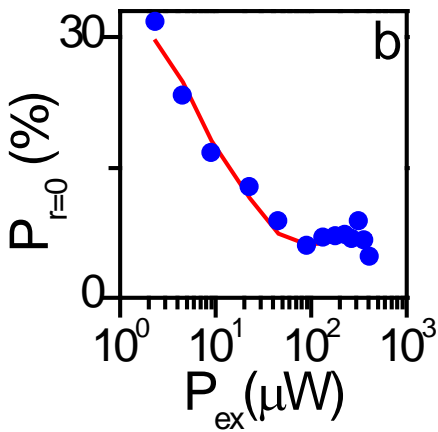
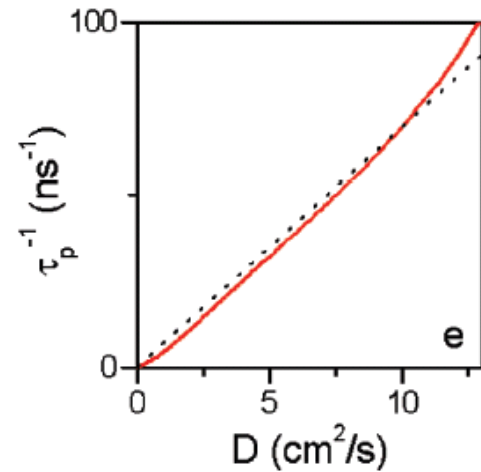
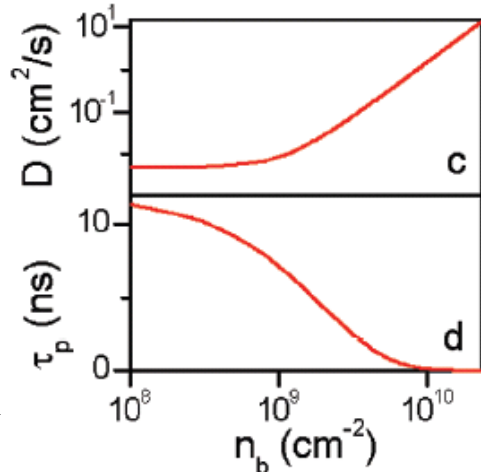
**GaAs CQW**  
**indirect exciton**  
with small  $e$ - $h$  overlap  
 $\sim 0.1 \mu\text{eV}$

J.R. Leonard, Y.Y. Kuznetsova, Sen Yang, L.V. Butov,  
T. Ostatnický, A. Kavokin, A.C. Gossard, Nano Lett. 9,  
4204 (2009)

# Density dependence



$$r_{\text{cloud}} \sim (D\tau_r)^{1/2}$$

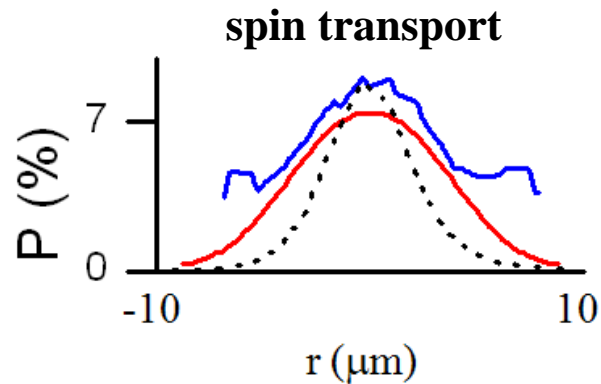


$$P = \frac{\tau_p}{\tau_p + \tau_r}$$

$P$  and  $\tau_p$  drop with increasing density (or  $T$ )

decrease of  $\tau_p$  is correlated with the increase  $D$   
 $\rightarrow \tau_p$  drops when excitons become delocalized

**complies with D'yakonov - Perel' spin relaxation mechanism**



## Decrease of $P$ and $\tau_p$ with increasing density

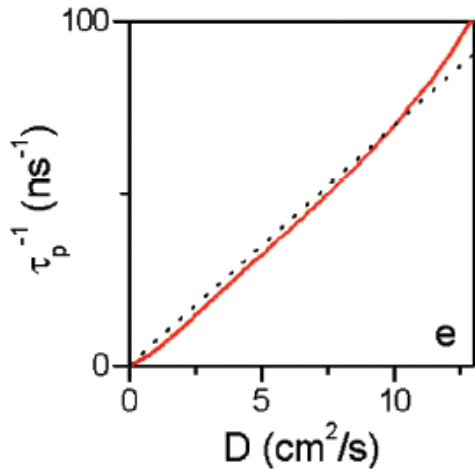
**complies with D'yakonov-Perel' spin relaxation mechanism**

spin relaxation time  $\tau_e^{-1} = \langle \Omega_e^2 \tau \rangle$

$\Omega_e = 2\beta k / \hbar$  frequency of spin precession

$\tau \approx m_{ex} D / k_B T$  momentum scattering time

$k_T = (2m_{ex} k_B T / \hbar^2)^{1/2} m_e / m_{ex}$



$$\tau_p^{-1} = 2\tau_e^{-1} = 16\beta^2 m_e^2 D / \hbar^4$$

**spin splitting constant**

**experiment:**  $\beta \approx 25$  meVÅ

**theoretical estimate:**  $\beta \approx 20$  meVÅ



# **Topological defects in interference pattern**

# Vortices

**quantized vortex is characterized by point (or line)  
around which phase of wave function varies by  $2\pi n$**



**fork-like dislocation in phase pattern is signature of quantized vortex**

## quantized atom vortices

S. Inouye, S. Gupta, T. Rosenband, A.P. Chikkatur, A. Görlitz, T.L. Gustavson, A.E. Leanhardt, D.E. Pritchard, W. Ketterle, PRL 87, 080402 (2001)

F. Chevy, K.W. Madison, V. Bretin, J. Dalibard, PRA 64, 031601(R) (2001)

Z. Hadzibabic, P. Krüger, M. Cheneau, B. Battelier, J. Dalibard, Nature 441, 1118 (2006)

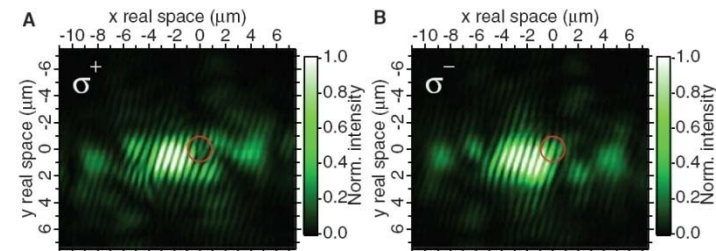
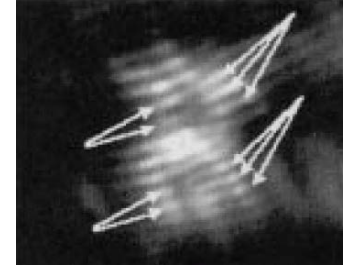
## quantized optical vortices

J. Scheuer, M. Orenstein, Science 285, 230 (1999)  
and references therein

## quantized polariton vortices

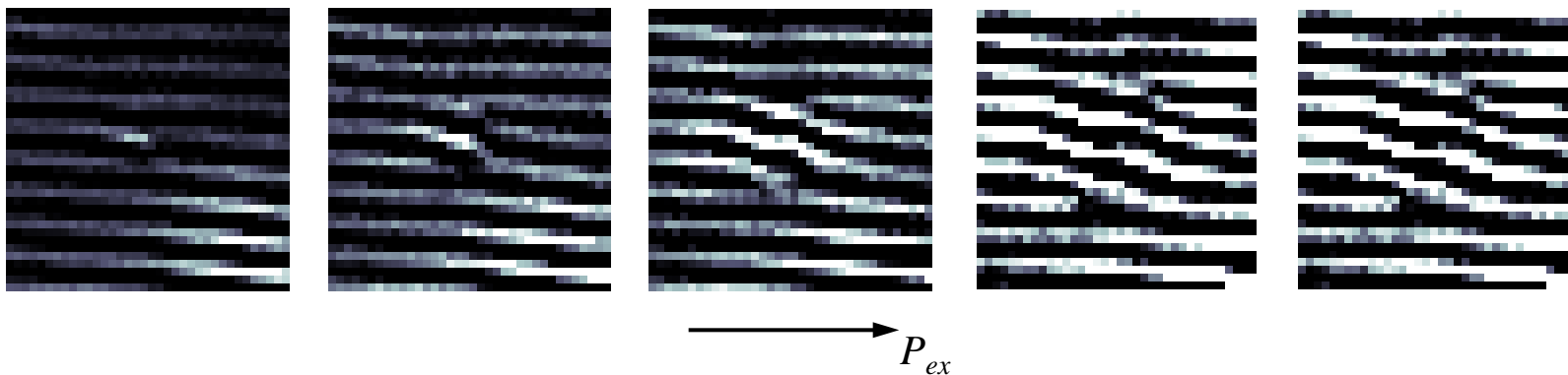
K.G. Lagoudakis, M. Wouters, M. Richard, A. Baas, I. Carusotto, R. André, Le Si Dang, B. Deveaud-Plédran, Nature Physics 4, 706 (2008)

K.G. Lagoudakis, T. Ostatnický, A.V. Kavokin, Y.G. Rubo, R. André, B. Deveaud-Plédran, Science 326, 974 (2009)

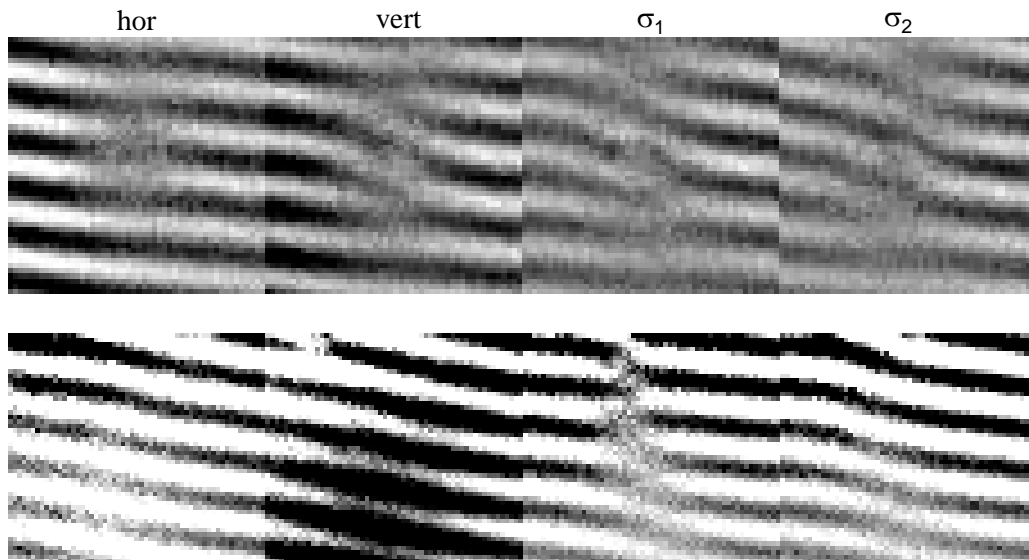


**polariton half-vortices**

# Fork-like topological defects in interference pattern of indirect excitons



for different polarizations



**theoretical study of topological defects in multicomponent spin excitonic systems**

Y.G. Rubo, PRL 99, 106401 (2007)

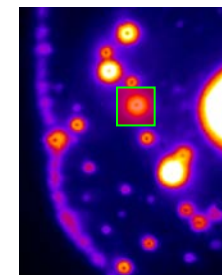
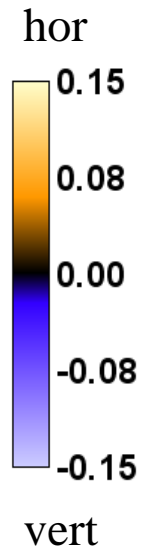
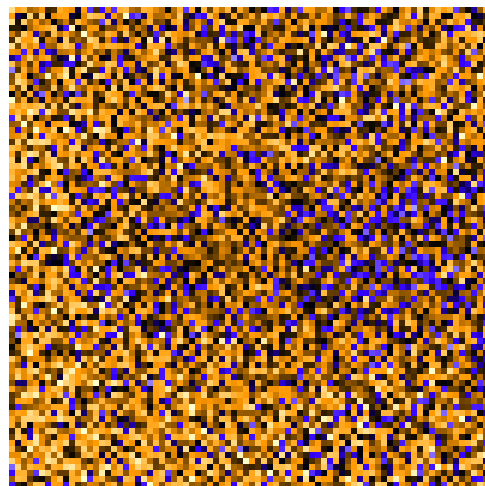
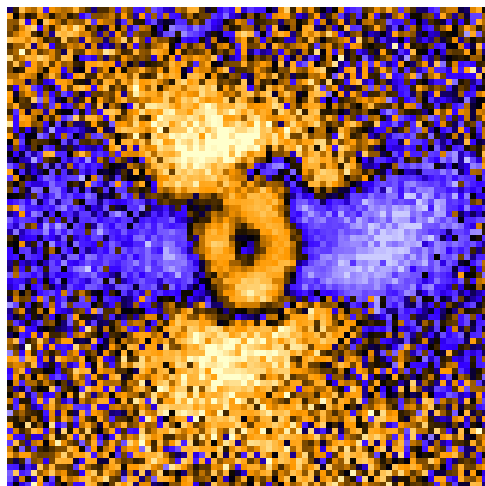
A.A. High, A.T. Hammack, J.R. Leonard, L.V. Butov, T. Ostatnicky', A. Kavokin, Y.G. Rubo, A.C. Gossard, unpublished

# Spin pattern formation

# Linear polarization

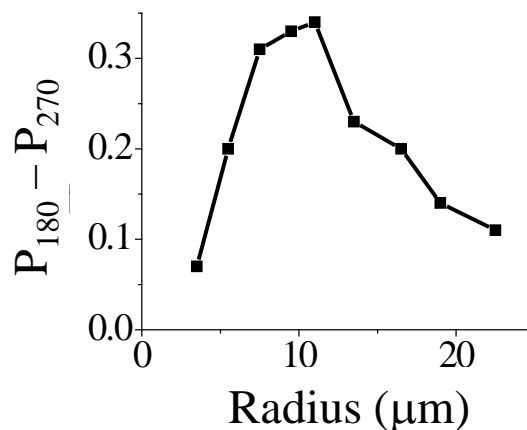
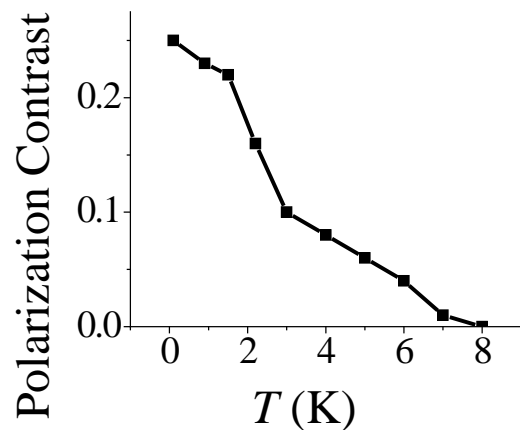
base  $T$

$T = 7$  K



**Data:**

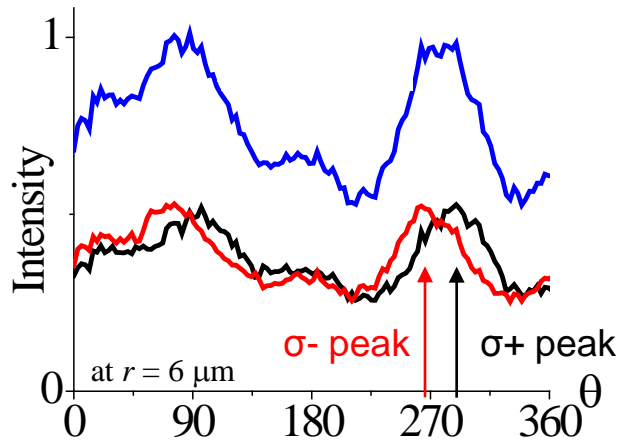
- polarization rings
- polarization vortex: linear polarization is perpendicular to radial direction



**Pattern of linear polarization**

- forms spontaneously
- is observed up to large distances from the origin
- is observed at low  $T$

# Circular polarization

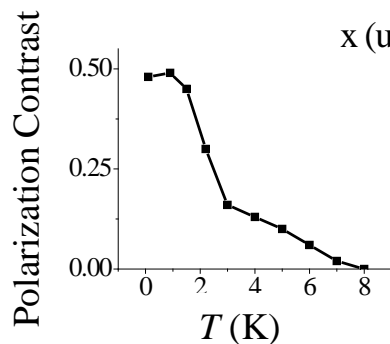
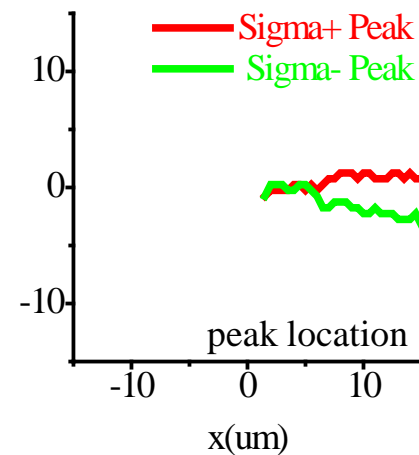
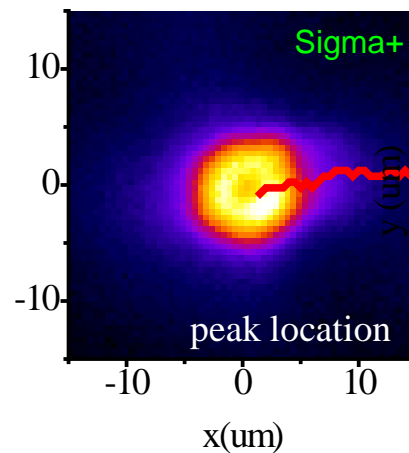
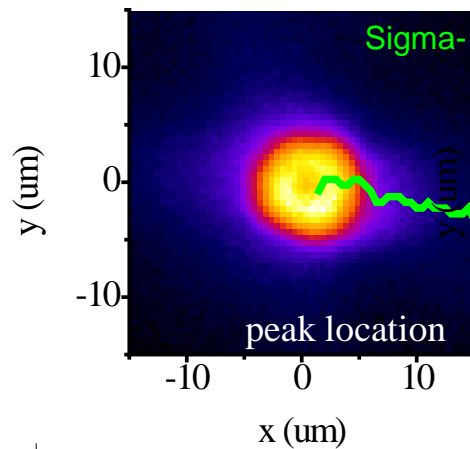
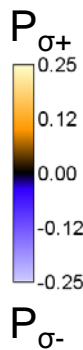
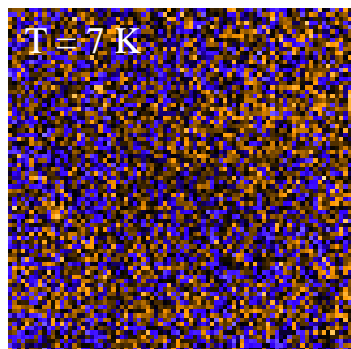
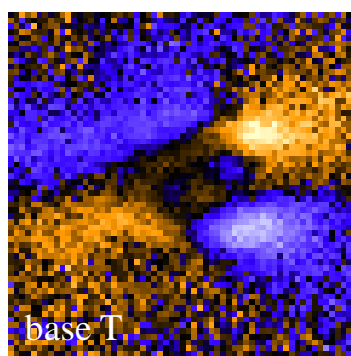


## Data:

- skew of circular polarized fluxes around  $90^\circ$  and  $270^\circ$

## Pattern of circular polarization

- forms spontaneously
- is observed up to large distances from the origin
- is observed at low  $T$



# Experiments on cold excitons in CQW

- Realized cold exciton gases with  $T \ll T_{dB}$

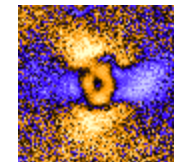
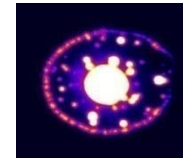
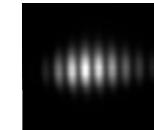
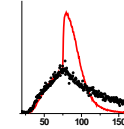
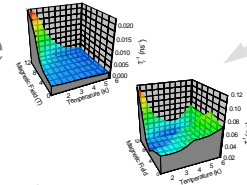
- Observed in cold exciton gases:

- Evidence for phenomena expected for exciton BEC

enhancement  
of exciton

- radiative decay rate → superradiance
- mobility → superfluidity
- scattering rate with increasing density → stimulated scattering
- coherence length → spontaneous coherence

consistent with onset of



not discussed  
in this presentation

PRL 73, 304 (1994)  
PRB 58, 1980 (1998)

PRL 86, 5608 (2001)

PRL 97, 187402 (2006)

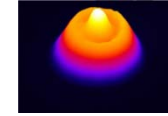
Nature 418, 751 (2002)

- Macroscopically ordered exciton state
- Topological defects in interference pattern
- Spin pattern formation

# Control of cold excitons

- **Excitons in laser induced traps**

- Trapping of cold excitons in laser-induced traps
- Hierarchy of times  $\tau_{cool} \ll \tau_{load} \ll \tau_{rec}$  is favorable for control of cold excitons

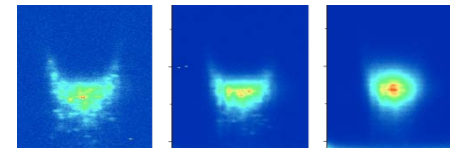


PRL 96, 227402 (2006)

PRB 76, 193308 (2007)

- **Excitons in electrostatic traps**

- Exciton collection to trap center with increasing density, screening of disorder, realization of cold exciton gas at trap center
- Evaporative cooling of excitons in elevated traps

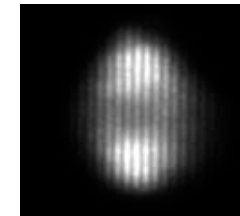


Nano Lett. 9,  
2094 (2009)

PRL 103, 087403  
(2009)

- **Excitons in lattices**

- Localization-delocalization transition with reducing lattice amplitude or increasing exciton density
- Estimating strength of disorder and exciton interaction

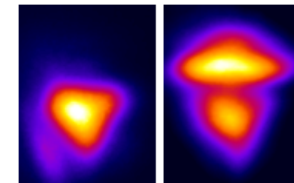


PRL 102, 186803  
(2009)

## Excitonic devices

- **Excitonic transistor**

- Prototype performs switching at speeds  $> 1$  GHz
- Compact:  $3 \mu\text{m}$  between source and drain
- Scalable: have architecture and operation principle similar to FET
- Operation of excitonic switches at  $\sim 100$  K



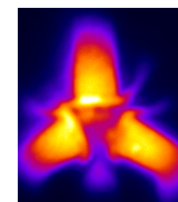
Opt. Lett. 32, 2466  
(2007)

Science 321, 229  
(2008)

Nature Photonics 3,  
577 (2009)

- **Simple excitonic integrated circuits**

- Prototype performs directional switching and merging



Opt. Lett. 35, 1587  
(2010)



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**Martin Griswold**

**Mikas Remeika**

**Sen Yang**

**Yuliya Kuznetsova**

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**Arthur Gossard, *UCSB***

**Atac Imamoglu, *UCSB***

**Alexei Ivanov, *Cardiff***

**Alexey Kavokin, *Southampton***

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